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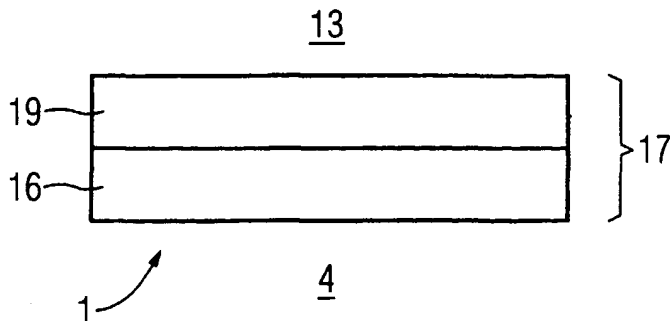
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(54) Title: HIGHLY OXIDATION RESISTANT COMPONENT



(57) ~~Abstract:~~ An oxidation resistant component 1 is disclosed comprising a substrate 4 and a protective layer 17. The protective layer 17 consists of an inner MCrAlY layer 16 contiguous with the substrate 4 and an outer MCrAlY layer 19. The outer layer 19 is characterized by having an Al content of up to 6.5 wt. % and by having the structure of a pure γ -Ni phase.

WO 2004/005580 A1